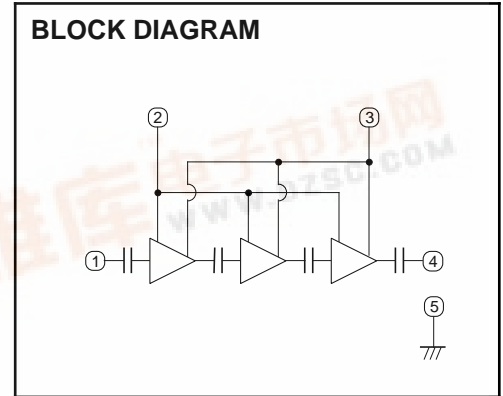
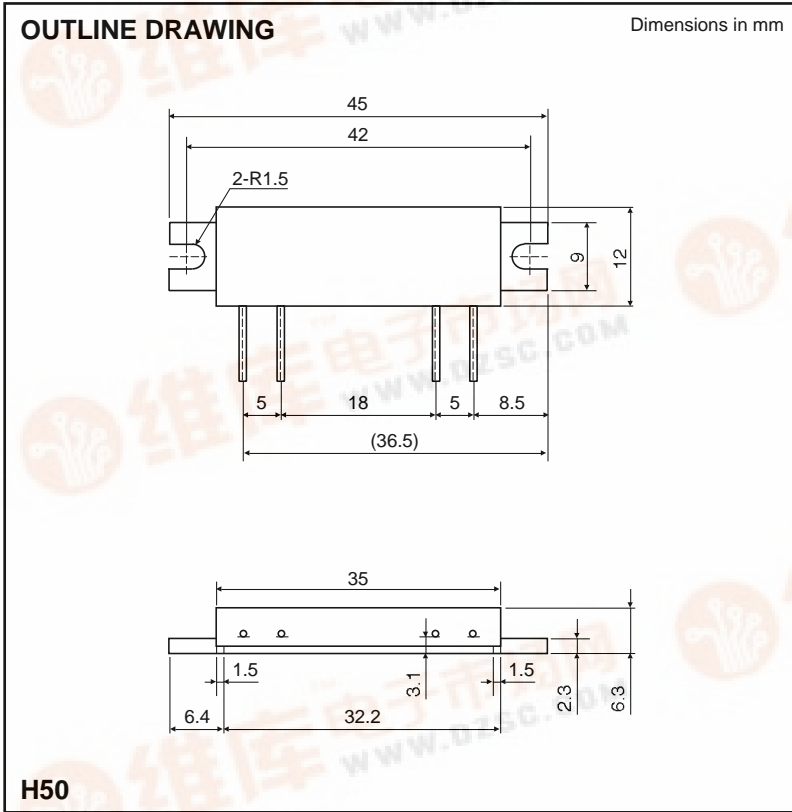


MITSUBISHI RF POWER MODULE

M68745H

SILICON MOS FET POWER AMPLIFIER, 896-941MHz, 3.8W, FM PORTABLE RADIO



PIN:

- ①Pin : RF INPUT
- ②VGG : GATE BIAS SUPPLY
- ③VDD : DRAIN BIAS SUPPLY
- ④Po : RF OUTPUT
- ⑤GND: FIN

ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

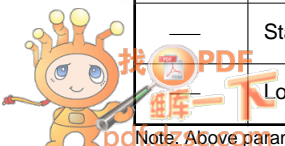
Symbol	Parameter	Conditions	Ratings	Unit
VDD	Supply voltage	ZG=ZL=50	9	V
VGG	Gate bias voltage		5.5	V
Pin	Input power	f=896-941MHz, ZG=ZL=50	6	mW
Po	Output power	f=896-941MHz, ZG=ZL=50	6	W
Tc (OP)	Operation case temperature	f=896-941MHz, ZG=ZL=50	-30 to +100	°C
Tstg	Storage temperature		-40 to +100	°C

Note. Above parameters are guaranteed independently.

ELECTRICAL CHARACTERISTICS (Tc=25°C, ZG=ZL=50 unless otherwise noted)

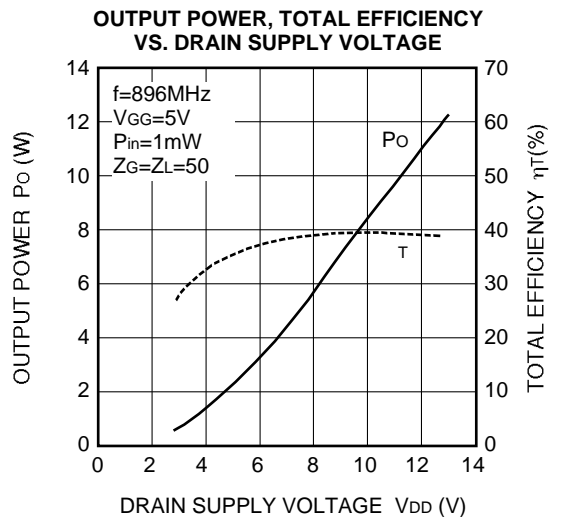
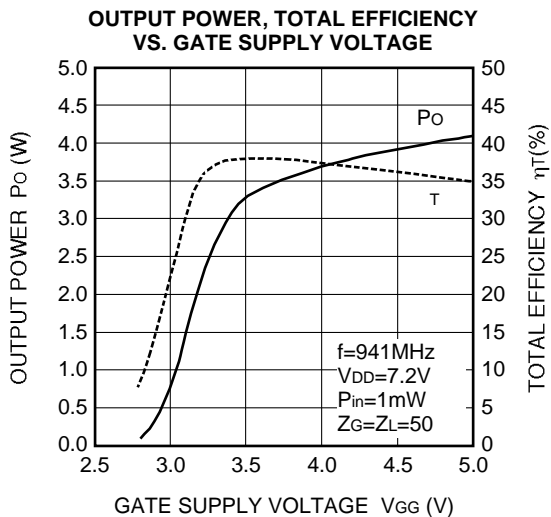
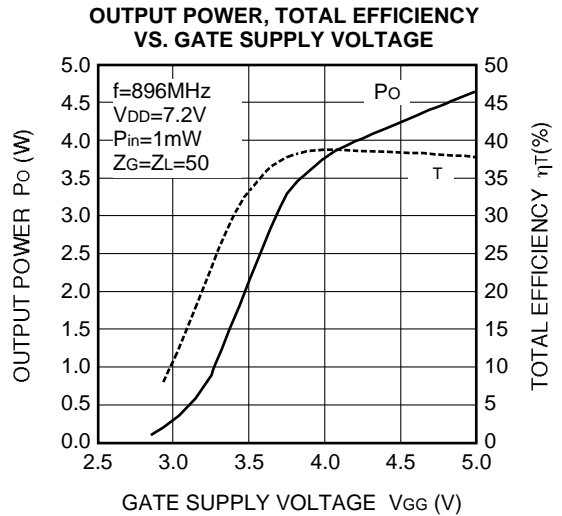
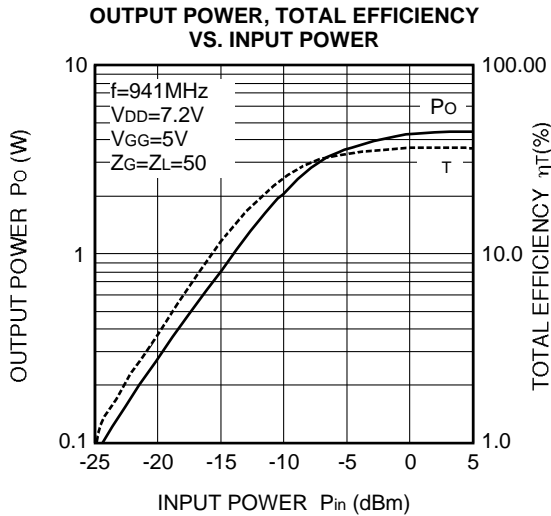
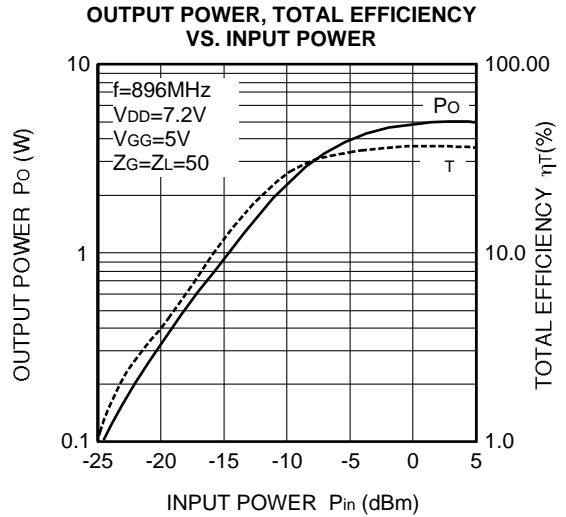
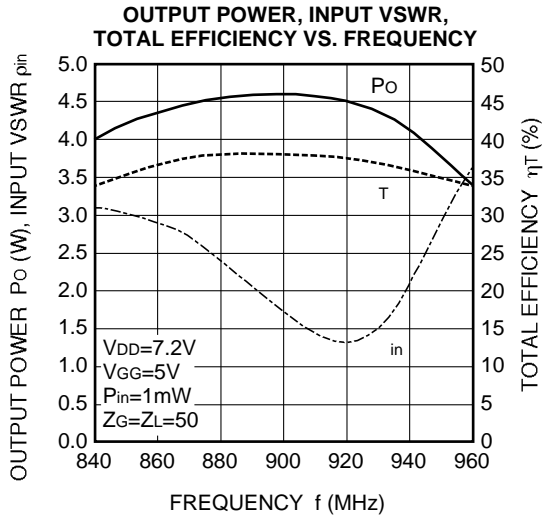
Symbol	Parameter	Test conditions	Limits		Unit
			Min	Max	
f	Frequency range		896	941	MHz
Po	Output power	VDD=7.2V, VGG=5V, Pin=1mW, ZG=ZL=50	3.8		W
2fo	2nd. harmonic			-30	dBc
in	Input VSWR			4	—
T	Total efficiency	PO=3.8W(VGG=Adjust), VDD=7.2V, Pin=1mW, ZG=ZL=50	30		%
—	Stability	ZG=ZL=50, VDD=5-9.3V, Load VSWR <4:1	No parasitic oscillation		—
—	Load VSWR tolerance	VDD=9V, Pin=1mW, PO=3.8W (VGG Adjust), ZL=20:1	No degradation or destroy		—

Note. Above parameters, ratings, limits and test conditions are subject to change.



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TYPICAL PERFORMANCE DATA



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